BRS	1	((oxidation near (reverse or reversal or reversing)) with metal) and (("2!	US-PGPUB; USPAT	6/6/05
BRS	7	("6204192"|"6319842"|"20010049181"|"20020098685"|"20020167089"|":	US-PGPUB; USPAT	6/6/05
BRS	6	S8 and ((cu or copper) near (reduce or reduction or reduced))	US-PGPUB; USPAT	6/6/05
BRS	0	S8 and (((cu or copper or cupric) adj oxide) with ((reduce or reduction o	US-PGPUB; USPAT	6/6/05
BRS	7	S13 and (((cu or copper or cupric) adj oxide) with ((reduce or reduction	US-PGPUB; USPAT	6/6/05
BRS	7	S14 not S9	US-PGPUB; USPAT	6/6/05
BRS	0	(hineman and russell).in.	US-PGPUB; USPAT	6/6/05
BRS	0	(hineman and russell).in.	EPO; JPO; DERWENT	6/6/05
BRS	24	(hineman or russell).in. and micron.as.	EPO; JPO; DERWENT	6/6/05
BRS	21	(hineman).in. and micron.as.	EPO; JPO; DERWENT	6/6/05
BRS	25	(hineman).in. and micron.as.	US-PGPUB; USPAT	6/6/05
BRS	3	S23 and damascene	US-PGPUB; USPAT	6/6/05
BRS	6	S25 and damascene	US-PGPUB; USPAT	6/6/05
BRS	4	(rathi and xu and huang).in.	US-PGPUB; USPAT	6/6/05
BRS	4	S29 and (@ad<"20040130" or @rlad<"20040130")	US-PGPUB; USPAT	6/6/05
BRS	33	S34 and (("257"/$3.cor.) or ("438"/$3.cor.))	US-PGPUB; USPAT	6/13/05
BRS	10	(plasma with hydrogen with ((before or prior) near2 barrier))	US-PGPUB; USPAT	6/13/05
BRS	10	S36 and (cu or copper)	US-PGPUB; USPAT	6/13/05
BRS	5	S36 and damascene	US-PGPUB; USPAT	6/13/05
BRS	2	6645852	US-PGPUB; USPAT	6/13/05
BRS	33	S43 and (cu or copper)	US-PGPUB; USPAT	6/13/05
BRS	10	S44 and damascene	US-PGPUB; USPAT	6/13/05
BRS	8	S45 and (@ad<"20040130" or @rlad<"20040130")	US-PGPUB; USPAT	6/13/05
BRS	19	S48 and (("257"/$3.cor.) or ("438"/$3.cor.))	US-PGPUB; USPAT	6/13/05
BRS	2	S49 and damascene	US-PGPUB; USPAT	6/13/05
BRS	9	S49 and (cu or copper)	US-PGPUB; USPAT	6/13/05
BRS	7	S51 not S50	US-PGPUB; USPAT	6/13/05
BRS	14	(damascene with (etch or etched or etching) with performed with chamt	US-PGPUB; USPAT	6/16/05
BRS	7	(damascene with (etch or etched or etching) with ((one or single) adj ch	US-PGPUB; USPAT	6/16/05
BRS	1	S60 not S59	US-PGPUB; USPAT	6/16/05
BRS	22	S62 and damascene	US-PGPUB; USPAT	6/16/05

BRS	6	((chamber or vaccum) with (barrier near2 (remove or removed)) with p	US-PGPUB; USPAT	6/16/05
BRS	21	5861675	US-PGPUB; USPAT	6/16/05
BRS	7	(((tungsten adj nitride) or wn) with (copper or cu or damascene) with (di	US-PGPUB; USPAT	6/16/05
BRS	9	((parasitic adj (capacitor or capacitance)) with ("between" adj (interconn	US-PGPUB; USPAT	6/21/05
BRS	3	((parasitic adj (capacitor or capacitance)) with ("between" adj (interconn	US-PGPUB; USPAT	6/21/05
BRS	5	((parasitic adj (capacitor or capacitance)) with ("between" adj (interconn	US-PGPUB; USPAT	6/21/05
BRS	7	(micron.as.) and (microprocessor.clm.) and damascene	US-PGPUB; USPAT	6/21/05
BRS	27	(microprocessor.clm.) and damascene	US-PGPUB; USPAT	6/21/05
BRS	20	S77 not S76	US-PGPUB; USPAT	6/21/05
BRS	33	S79 and (("257"/$3.cor.) or ("438"/$3.cor.))	US-PGPUB; USPAT	6/21/05
BRS	32	S80 and (@ad<"20040130" or @rlad<"20040130")	US-PGPUB; USPAT	6/21/05
BRS	3	S81 and damascene	US-PGPUB; USPAT	6/21/05
BRS	19	S85 and (("257"/$3.cor.) or ("438"/$3.cor.)) and (@ad<"20040130" or @	US-PGPUB; USPAT	6/21/05
BRS	0	S87 and (("257"/$3.cor.) or ("438"/$3.cor.)) and (@ad<"20040130" or @	US-PGPUB; USPAT	6/21/05
BRS	4	S89 and (("257"/$3.cor.) or ("438"/$3.cor.)) and (@ad<"20040130" or @	US-PGPUB; USPAT	6/21/05
BRS	4	S92 and (("257"/$3.cor.) or ("438"/$3.cor.)) and (@ad<"20040130" or @	US-PGPUB; USPAT	6/23/05
BRS	11	(US-20010034127-$ or US-20020111037-$ or US-20020177303-$).did.	US-PGPUB; USPAT	6/23/05
BRS	0	S99 and triple	US-PGPUB; USPAT	6/23/05
BRS	6	S118 and (("257"/$3.cor.) or ("438"/$3.cor.))	US-PGPUB; USPAT	6/23/05
BRS	0	S123 and (("428"/$3.cor.))	US-PGPUB; USPAT	6/23/05
BRS	19	integrated adj circuit adj coupled adj microprocessor	US-PGPUB; USPAT	6/23/05
BRS	12	integrated adj circuit adj connected adj microprocessor	US-PGPUB; USPAT	6/23/05
BRS	2	S135 and damascene	US-PGPUB; USPAT	6/23/05
BRS	4	S135 and (microprocessor with ("same" adj (chip or substrate)))	US-PGPUB; USPAT	6/23/05
BRS	0	S142 and (("428"/$3.cor.))	US-PGPUB; USPAT	6/23/05
BRS	6	S142 and semiconductor	US-PGPUB; USPAT	6/23/05
BRS	0	S148 and (("257"/$3.cor.) or ("438"/$3.cor.))	US-PGPUB; USPAT	6/23/05
BRS	3	S148 and semiconductor	US-PGPUB; USPAT	6/23/05
BRS	0	S156 and (("257"/$3.cor.) or ("438"/$3.cor.))	US-PGPUB; USPAT	6/23/05
BRS	21	(t$1boc or tboc) and (("257"/$3.cor.) or ("438"/$3.cor.))	US-PGPUB; USPAT	6/25/05
BRS	4	((hf or hydro$1fluoric)) and S158	US-PGPUB; USPAT	6/23/05

BRS	1	(t$1boc or tboc) and S160	US-PGPUB; USPAT	6/25/05
BRS	1	((hf or hydro$1fluoric) with (resist or photo$1resist) with best)	US-PGPUB; USPAT	6/25/05
BRS	0	((hf or hydro$1fluoric) with (resist or photo$1resist) with superb)	US-PGPUB; USPAT	6/25/05
BRS	14	((hf or hydro$1fluoric) with (resist or photo$1resist) with good)	US-PGPUB; USPAT	6/25/05
BRS	0	((hf or hydro$1fluoric) with (resist or photo$1resist) with "since")	US-PGPUB; USPAT	6/25/05
BRS	5	((hf or hydro$1fluoric) with (resist or photo$1resist) with quick)	US-PGPUB; USPAT	6/25/05
BRS	1	S170 and damascene	US-PGPUB; USPAT	6/25/05
BRS	1	S168 and damascene	US-PGPUB; USPAT	6/25/05
BRS	1	S167 and damascene	US-PGPUB; USPAT	6/25/05
BRS	4	S174 and damascene	US-PGPUB; USPAT	6/25/05
BRS	30	((microprocessor) with ("same" adj (chip or substrate)) with embedded	US-PGPUB; USPAT	6/25/05
BRS	30	S180 and (@ad<"20040130" or @rlad<"20040130")	US-PGPUB; USPAT	6/25/05
BRS	3	S181 and (("257"/$3.cor.) or ("438"/$3.cor.))	US-PGPUB; USPAT	6/25/05
BRS	14	S184 and (("257"/$3.cor.) or ("438"/$3.cor.))	US-PGPUB; USPAT	6/25/05
BRS	4	(memory with damascene with density)	US-PGPUB; USPAT	6/25/05
BRS	9	(memory with damascene with resistance)	US-PGPUB; USPAT	6/25/05